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September 2016

## FDD3860

# N-Channel PowerTrench® MOSFET 100 V, 29 A, 36 m $\Omega$

#### **Features**

- Max  $r_{DS(on)} = 36 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 5.9 \text{ A}$
- High Performance Trench Technology for Extremely Low r<sub>DS(on)</sub>
- 100% UIL Tested
- RoHS Compliant

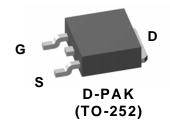


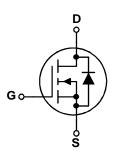
#### **General Description**

This N-Channel MOSFET is rugged gate version of Fairchild Semiconductor's advanced Power Trench<sup>®</sup> process. This part is tailored for low  $r_{DS(on)}$  and low Qg figure of merit, with avalanche ruggedness for a wide range of switching applications.

#### **Applications**

- DC-AC Conversion
- Synchronous Rectifier





### **MOSFET Maximum Ratings** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter			Ratings	Units
V <sub>DS</sub>	Drain to Source Voltage			100	V
$V_{GS}$	Gate to Source Voltage			±20	V
	Drain Current -Continuous	T <sub>C</sub> = 25°C		29	
I <sub>D</sub>	-Continuous T <sub>A</sub> = 25°C		(Note 1a)	6.2	Α
	-Pulsed			60	
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	121	mJ
В	Power Dissipation	T <sub>C</sub> = 25°C		83	W
$P_{D}$	Power Dissipation $T_A = 25^{\circ}C$ (Note 1a)		(Note 1a)	3.75	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Tempera	ture Range		-55 to +175	°C

#### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	40	C/VV

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD3860	FDD3860	D-PAK (TO-252)	13"	16 mm	2500 units

# **Electrical Characteristics** $T_J = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Chara	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, referenced to 25°C		98		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$			1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA

#### On Characteristics

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.5	3.8	4.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to 25°C		-11.4		mV/°C
-	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 5.9A$		29	36	mΩ
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 5.9A, T_J = 125$ °C		51	64	1115.2
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10V, I_D = 5.9A$		20		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 50V V 0V	1310	1740	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 50V, V_{GS} = 0V,$ f = 1MHz	100	130	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1101112	45	70	pF
$R_g$	Gate Resistance	f = 1MHz	1.6		Ω

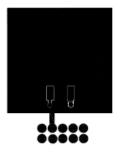
#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time	.,,		16	29	ns
t <sub>r</sub>	Rise Time	$V_{DD} = 50V, I_{D} = 5.9A,$ $V_{GS} = 10V, R_{GEN} = 6\Omega$		10	21	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10V, R_{GEN} = 022$		24	39	ns
t <sub>f</sub>	Fall Time			7	15	ns
$Q_g$	Total Gate Charge at 10V	V 50V L 50A		22	31	nC
$Q_{gs}$	Gate to Source Charge	V <sub>DD</sub> = 50V, I <sub>D</sub> = 5.9A		7.1		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			6.3		nC

#### **Drain-Source Diode Characteristics**

Ved Source to Drain Dioge Forward Voltage	$V_{GS} = 0V, I_S = 2.0A$ (Note 2)	0.7	1.2	\/	
	$V_{GS} = 0V, I_S = 5.9A$ (Note 2)	0.8	1.3	V	
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 5.9A, di/dt = 100A/μs	34	55	ns
Q <sub>rr</sub>	Reverse Recovery Charge	iF = 3.9A, αναί = 100A/μS	40	64	nC

Notes: 1:  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a) 40°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b) 96°C/W when mounted on a minimum pad.

- 2: Pulse Test: Pulse Width < 300  $\mu$ s, Duty cycle < 2.0%. 3: Starting T $_J$  = 25°C, L = 3mH, I $_{AS}$  = 9A, V $_{DD}$  = 100V, V $_{GS}$  = 10V.

### **Typical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted.

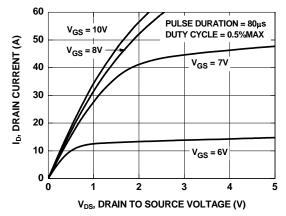


Figure 1. On-Region Characteristics

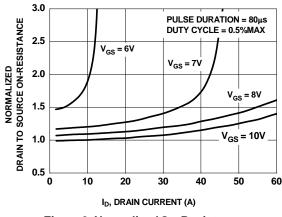


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

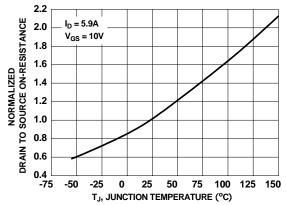


Figure 3. Normalized On-Resistance vs. Junction Temperature

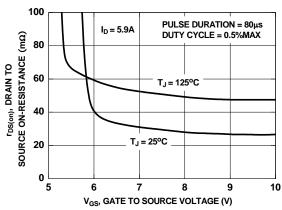


Figure 4. On-Resistance vs. Gate to Source Voltage

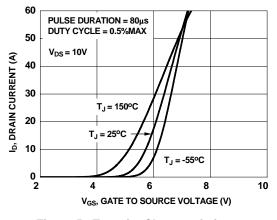


Figure 5. Transfer Characteristics

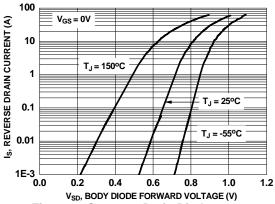


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

### **Typical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted.

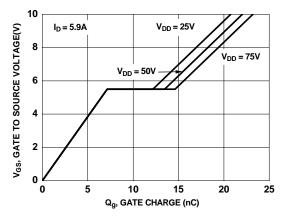


Figure 7. Gate Charge Characteristics

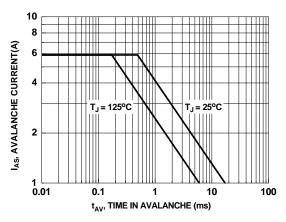


Figure 9. Unclamped Inductive Switching Capability

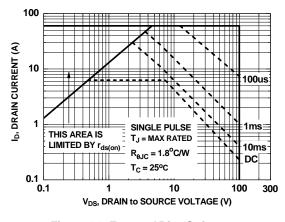


Figure 11. Forward Bias Safe Operating Area

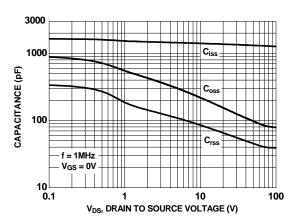


Figure 8. Capacitance vs. Drain to Source Voltage

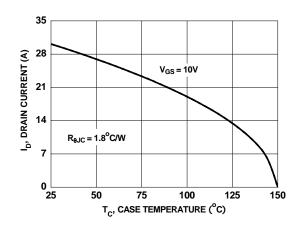


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

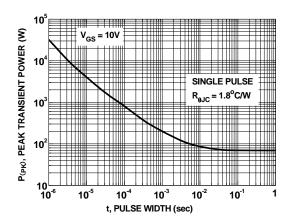


Figure 12. Single Pulse Maximum Power Dissipation



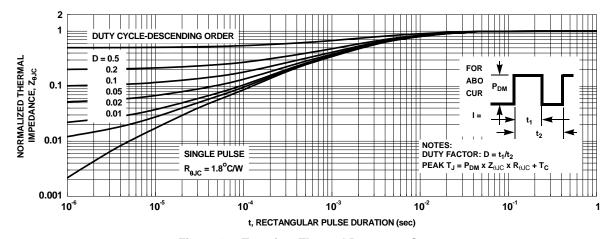


Figure 13. Transient Thermal Response Curve

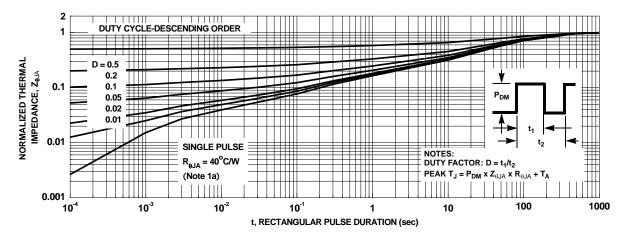


Figure 14. Transient Thermal Response Curve

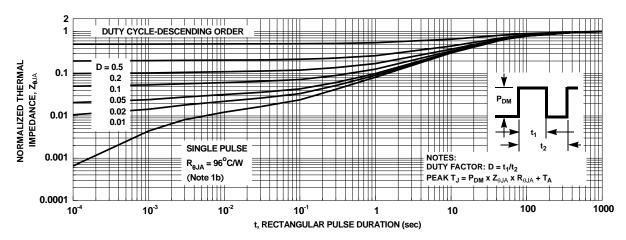


Figure 15. Transient Thermal Response Curve





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